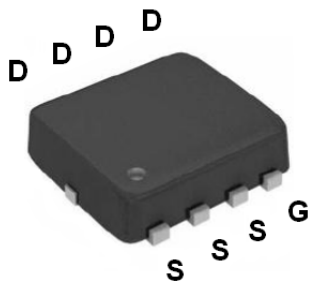
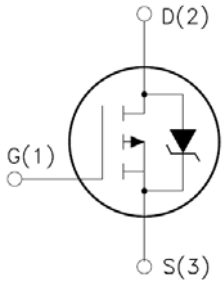
P-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ)
-30V	-35A	7.0mΩ





PDFN（3X3）

Features:

- Low Gate Charge for Fast Switching Application
- Low $R_{DS(ON)}$ to Minimize Conductive Loss
- Reliable and Rugged

Absolute Maximum Ratings (T_A = 25°C unless otherwise specifed)

Symbol	Parameter		Ratings	Unit
Common Ratings				
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to150	°C
I_S	Diode Continuous Forward Current	T_C =25°C	-30	A
Mounted on Large Heat Sink				
I_{DM}	300μs Pulse Drain Current Tested (2)	T_C=25°C, V_{GS}=-10V	-120	A
I_D	Continuous Drain Current (1)	T_C=25°C, V_{GS}=-10V	-35	A
		T_C=100°C V_{GS}=-10V	-19	A
P_D	Maximum Power Dissipation	T_C=25°C	27	W

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
R_{thJC}	Thermal resistance junction-case max (1)	3.6	°C/W
R_{thJA}	Thermal resistance junction-ambient max (1)	37	°C/W

Electrical Characteristics (TA=25°C Unless Otherwise Noted)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
On/off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=-250uA	-30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -27V, V_{GS}=0V T_J=25°C	--	--	-1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=-250uA	-1.2	-1.6	-2.0	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
$R_{DS(ON)}$	Drain-SourceOn-stateResistance(2)	V_{GS}= -10V, I_{DS}=-10A	--	7.0	10	mΩ
		V_{GS}= -4.5V, I_{DS}=-8A	--	12	15	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}= -15V, Frequency=1.0MHz	--	3450	--	pF
C_{oss}	Output Capacitance		--	410	--	
C_{rss}	Reverse Transfer Capacitance		--	251	--	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time(1)	V_{DD}=-15V, I_D= -1A, V_{GS}= -4.5V, R_{GEN}=2.7Ω	--	15.8	--	ns
t_r	Turn-on Rise Time(1)		--	28.8	--	
$t_{d(OFF)}$	Turn-off Delay Time(1)		--	46.9	--	
t_f	Turn-off Fall Time(1)		--	12.3	--	
Q_g	Total Gate Charge(1)	V_{DS}=-15V, V_{GS}= -10V, I_{DS}=-10A	--	43	--	nC
Q_{gs}	Gate-Source Charge(1)		--	8.4	--	
Q_{gd}	Gate-Drain Charge(1)		--	14	--	
Diode Characteristics						
V_{SD}	Diode Forward Voltage(2)	I_{SD} =-3A, V_{GS} = 0V ,T_J=25°C	--	-0.8	-1.0	V

NOTES:

1. Surface Mounted on 1in2 FR-4 board with 1oz.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

Typical Performance Characteristics

Figure 1: Continuous Drain Current vs. TC

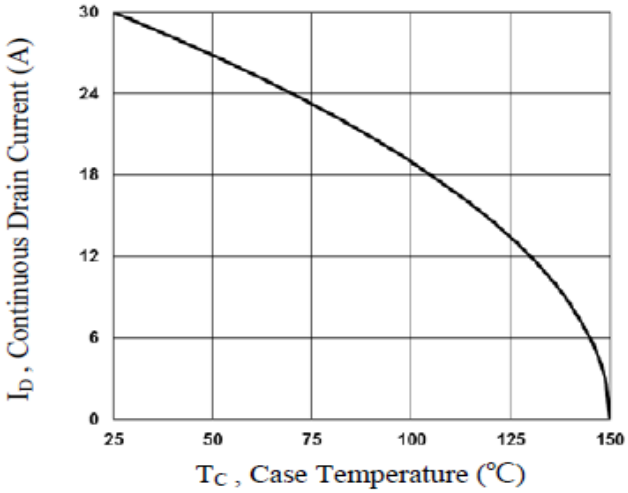


Figure 2: Normalized RDSON vs. TJ

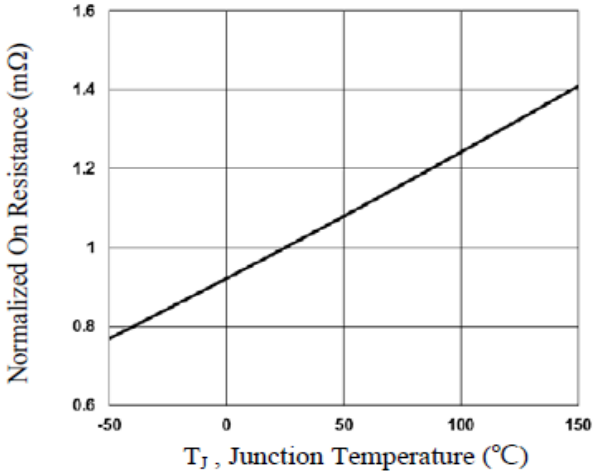


Figure 3: Normalized Vth vs. TJ

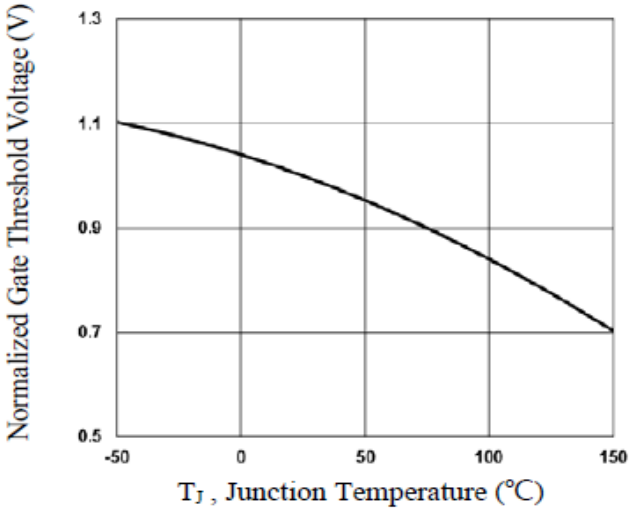


Figure 4: Maximum Safe Operating Area

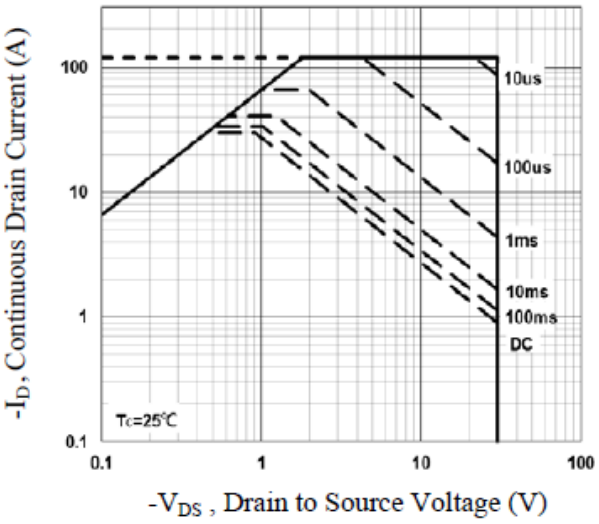


Figure 5: Normalized Transient Impedance

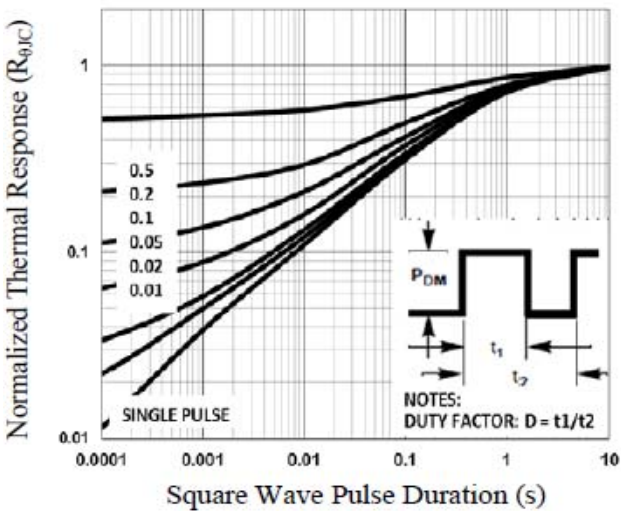
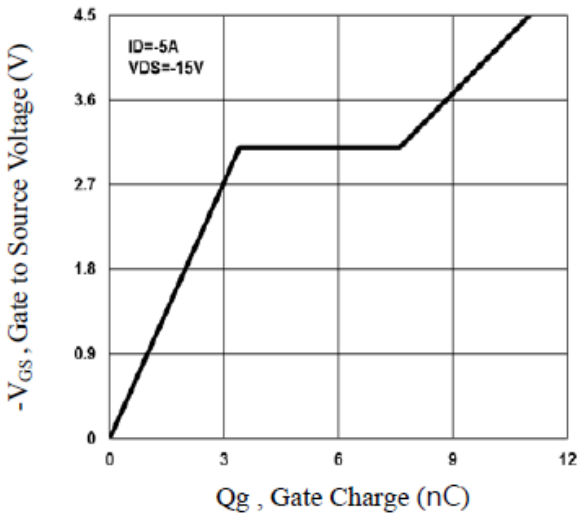
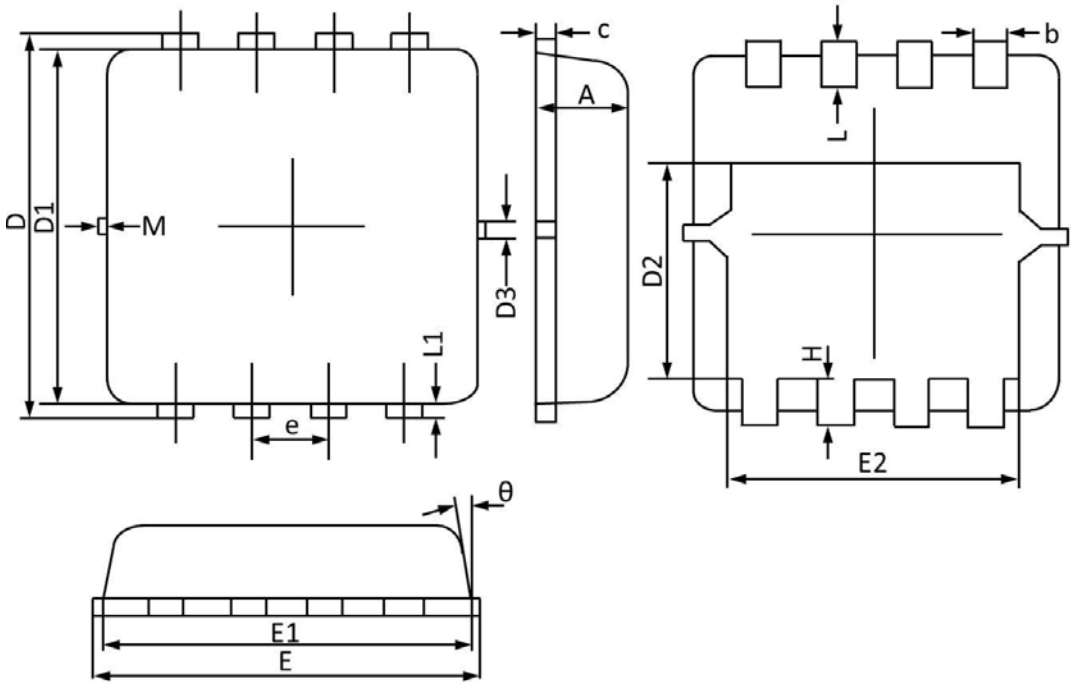


Figure 6: Gate Charge Characteristics



PACKAGE MECHANICAL DATA

PDFN（3X3） Package Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130REF		0.005REF	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
H	0.300	0.500	0.011	0.019
M	0.150REF		0.006REF	
e	0.650 TYP.		0.026 TYP.	
L	0.300	0.500	0.011	0.019
L1	0.130REF		0.005REF	
θ	0°	12°	0°	12°